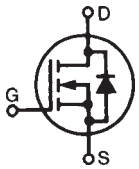
IXYS

PolarHV™ HiPerFET Power MOSFET

IXFB 60N80P

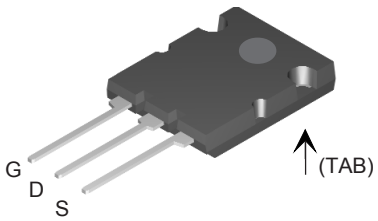
V_{DSS} = 800 V
I_{D25} = 60 A
$R_{DS(on)}$ ≤ 140 mΩ
t_{rr} ≤ 250 ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25° C to 150° C	800	V
V_{DGR}	T_J = 25° C to 150° C; R_{GS} = 1 MΩ	800	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25° C	60	A
I_{DM}	T_C = 25° C, pulse width limited by T_{JM}	150	A
I_{AR}	T_C = 25° C	30	A
E_{AR}	T_C = 25° C	100	mJ
E_{AS}	T_C = 25° C	5	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le$150° C, R_G = 2 Ω	20	V/ns
P_D	T_C = 25° C	1250	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10 s	260	°C
F_C	Mounting force	30..120/7.5...2.7	N/lb
Weight		10	g

PLUS264™ (IXFB)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Plus 264™ package for clip or spring
- Space savings
- High power density

Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 3 mA	800			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8 mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30 V_{DC}, V_{DS} = 0			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$			25	μA
	V_{GS} = 0 V T_J = 125° C			3000	μA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25}, Note 1			140	mΩ

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Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 20 V; I_D = 0.5 I_{D25}, Note 1	35	67		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		18		nF
C_{oss}			1200		pF
C_{rss}			44		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D =0.5 I_{D25} R_G = 1 Ω (External)		36		ns
t_r			29		ns
$t_{d(off)}$			110		ns
t_f			26		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		250		nC
Q_{gs}			90		nC
Q_{gd}			78		nC
R_{thJC}				0.10	°C/W
R_{thCS}			0.13		°C/W

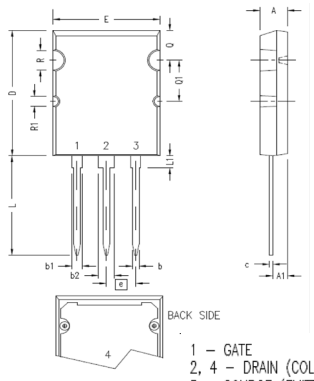
Source-Drain Diode

Symbol	Test Conditions (T_J = 25° C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			60	A
I_{SM}	Repetitive			150	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Note 1			1.5	V
t_{rr}	I_F = 25A, -di/dt = 100 A/μs			250	ns
Q_{RM}	V_R = 100V		0.6		μC
I_{RM}			6.0		A

Notes:

1. Pulse test, t ≤300 μs, duty cycle d≤ 2 %

PLUS264™ (IXFB) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or moreof the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405B2 6,710,463 6,727,585 6,759,692 6,771,478 B2

Fig. 1. Output Characteristics @ 25ºC

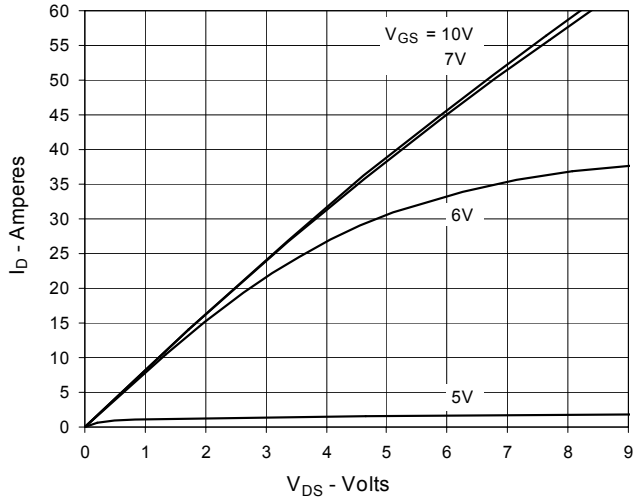


Fig. 2. Extended Output Characteristics @ 25ºC

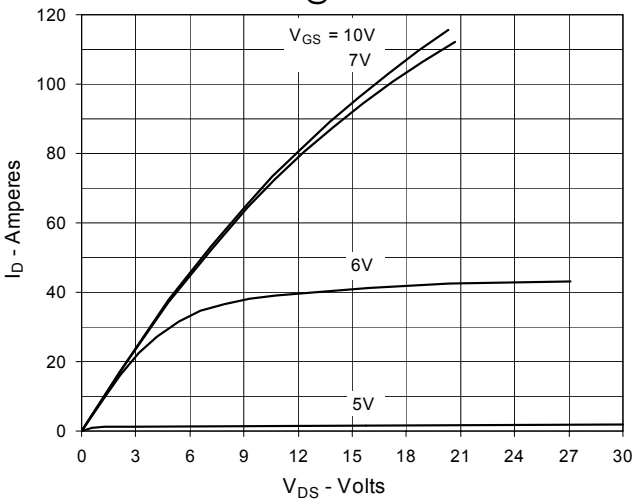


Fig. 3. Output Characteristics @ 125ºC

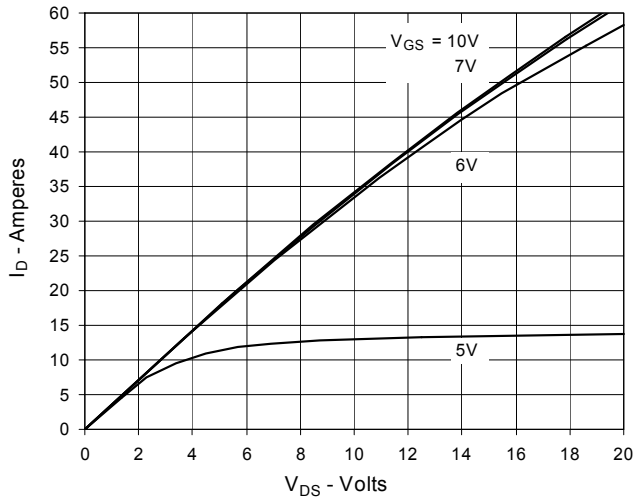


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 30A Value vs. Junction Temperature

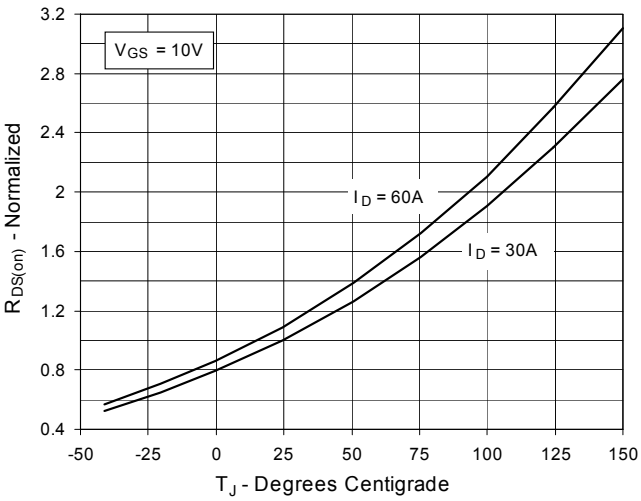


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 30A Value vs. Drain Current

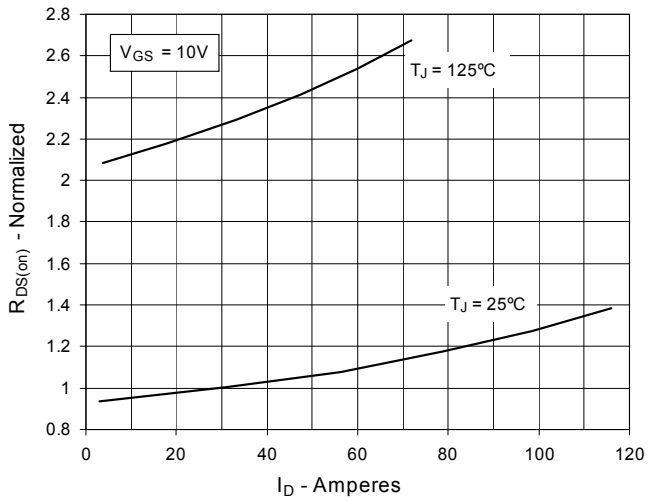
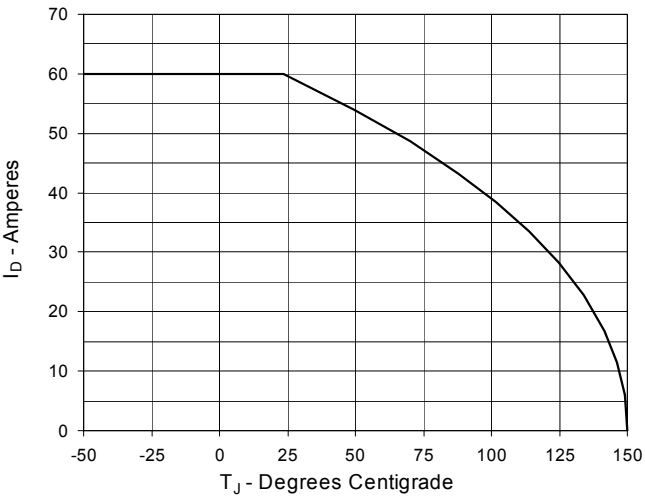


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

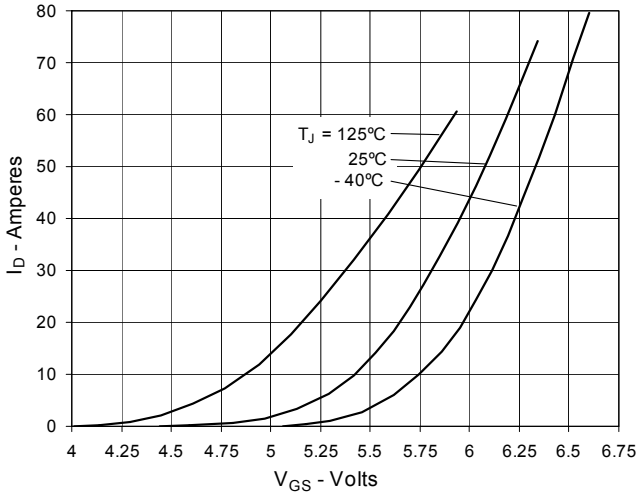


Fig. 8. Transconductance

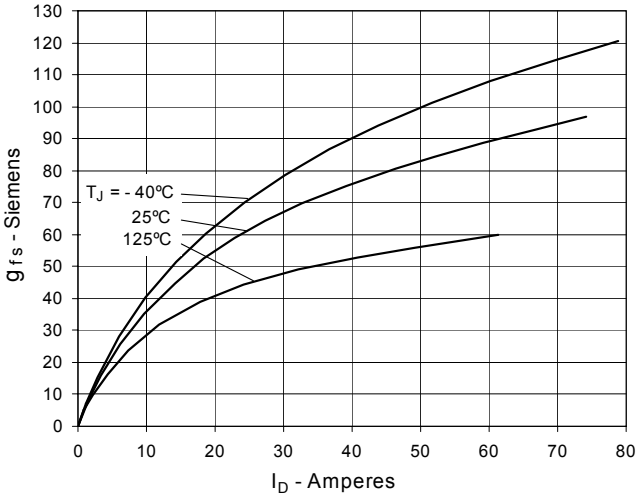


Fig. 9. Forward Voltage Drop of Intrinsic Diode

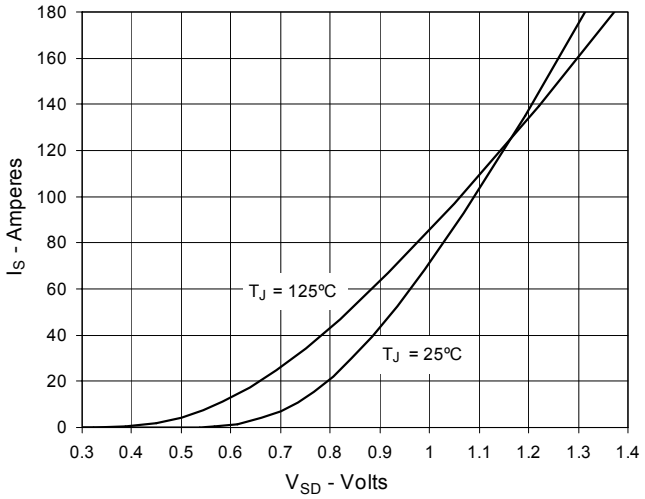


Fig. 10. Gate Charge

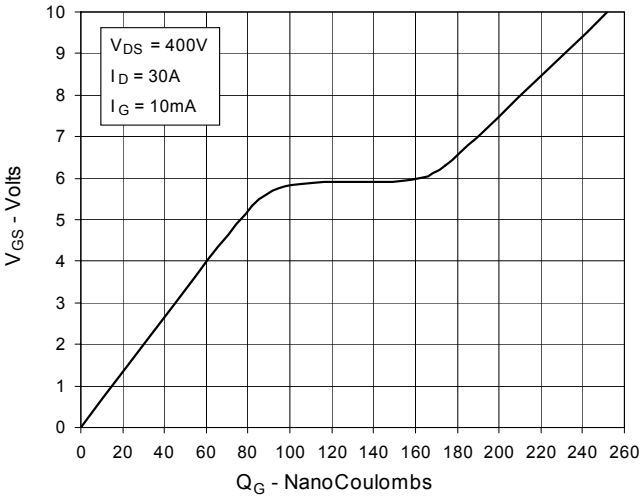


Fig. 11. Capacitance

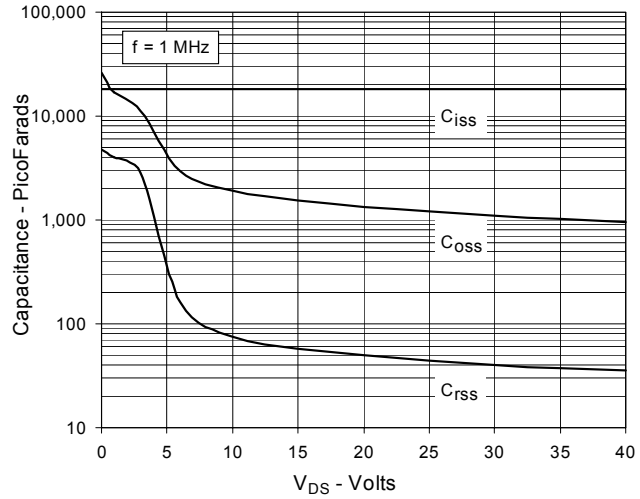
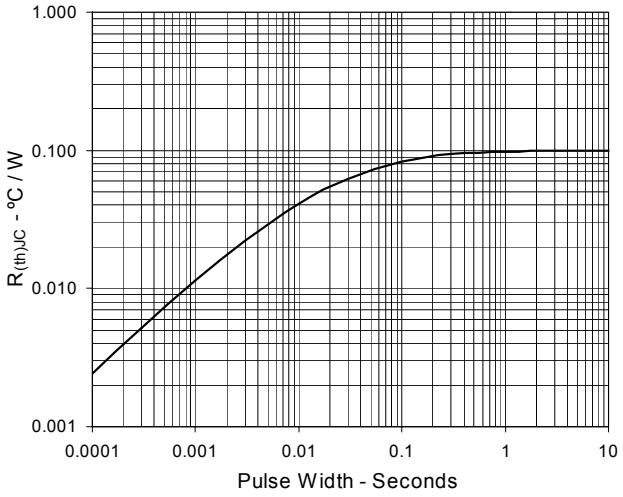


Fig. 12. Maximum Transient Thermal Resistance



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